Abstracts

Third-Order Nonlinearity of GaAs MESFET's

J.H. Abeles, S.H. Wemple, W.O.W. Schlosser and J.P. Beccone. "Third-Order Nonlinearity of GaAs MESFET's." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 224-226.

Direct linearity measurements at 6 GHz show that Bell Labs GaAs MESFET's are effectively third-order in AM/PM up to output powers near saturation, and that AM/AM can be made negligible through bias adjustment. This permits the use of predistortion techniques to attain extremely high linearity power amplification.

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